V_{DSS}	60 V
I_D	20 A
$R_{DS(ON)}$	26mΩ

Features

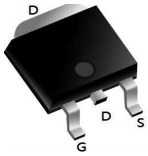
Excellent $R_{DS(ON)}$ and Low Gate Charge

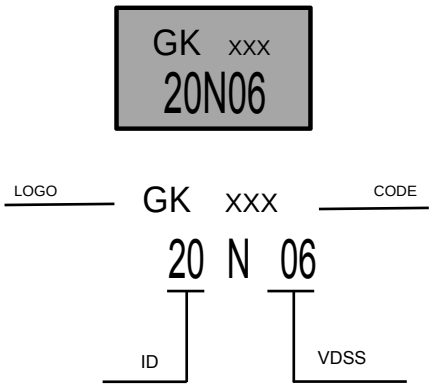
100% UIS Tested

100% ΔVds Tested

Halogen-free; RoHS-compliant

TO-252



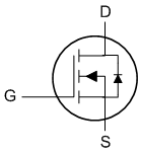


Applications

Load Switch

PWM Application

Power Management



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		60	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	20	A
		T_C = 100°C	12	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		24	mJ
P_D	Power Dissipation	T_C = 25°C	37	W
		T_C = 100°C	15	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	42	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.4	

Electrical Characteristics (T_J=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.1	1.6	2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 10A	-	26	33	mΩ
		V_{GS} = 4.5V, I_D = 5A	-	32	45	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	1.4	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 30V, f = 1MHz	848	1187	1602	pF
C_{oss}	Output Capacitance		40	56	76	pF
C_{rss}	Reverse Transfer Capacitance		34	47	63	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 30V, I_D = 10A	17	24	33	nC
Q_{gs}	Gate Source Charge		-	4.5	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	4.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 30V I_D= 10A, R_{GEN} = 3Ω	-	6.7	-	ns
t_r	Turn-On Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	24	-	ns
t_f	Turn-Off Fall Time		-	2.7	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	20	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	79	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 10A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 10A, di/dt = 100A/us	13	19	25	ns
Qrr	Body Diode Reverse Recovery Charge		-	19	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25C, V_{DD}=30V, V_{GS}=10V, R_G=25ohm, L=0.5mH, I_{AS}=9.8A, V_{DD}=0V during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

RATING AND CHARACTERISTIC CURVES

Figure 1: Power De-rating

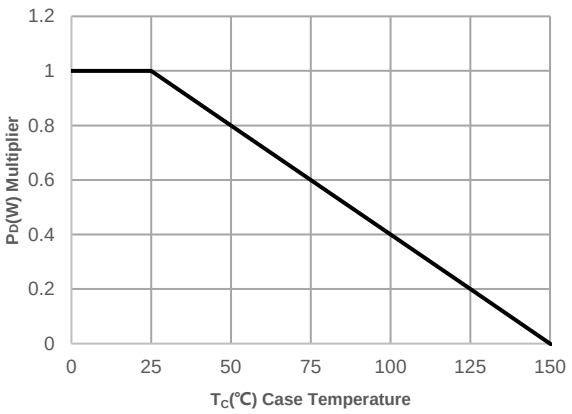


Figure 2: Current De-rating

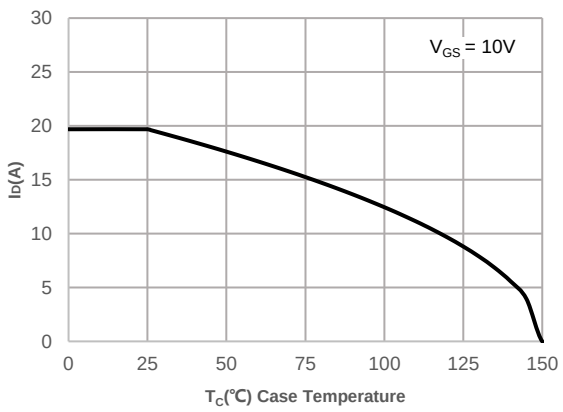


Figure 3: Normalized Maximum Transient Thermal Impedance

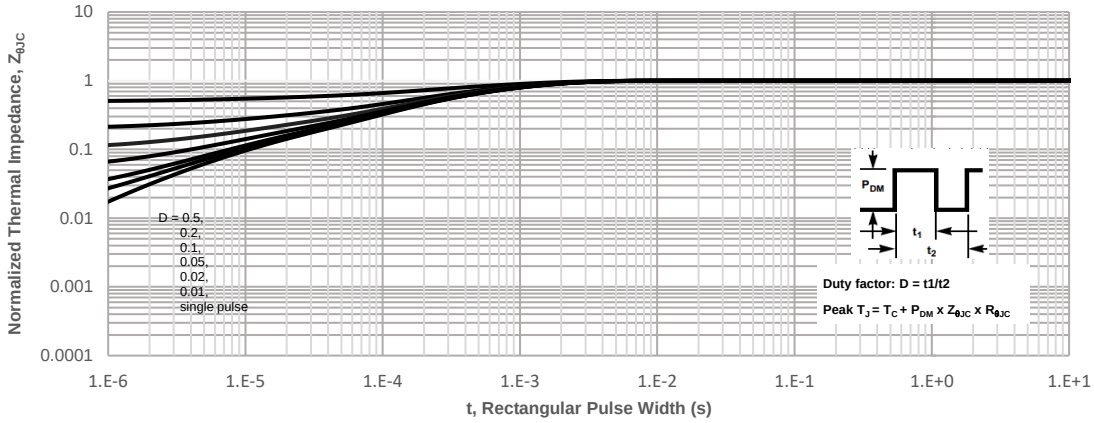
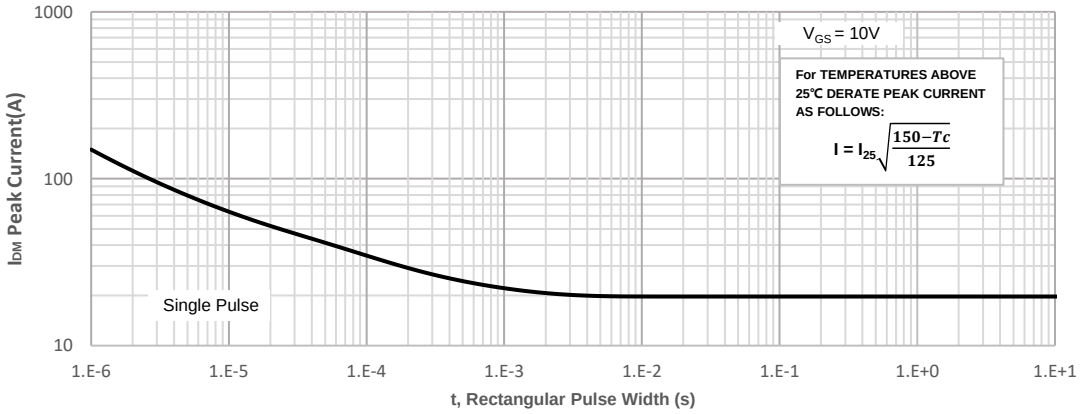


Figure 4: Peak Current Capacity



RATING AND CHARACTERISTIC CURVES

Figure 5: Output Characteristics

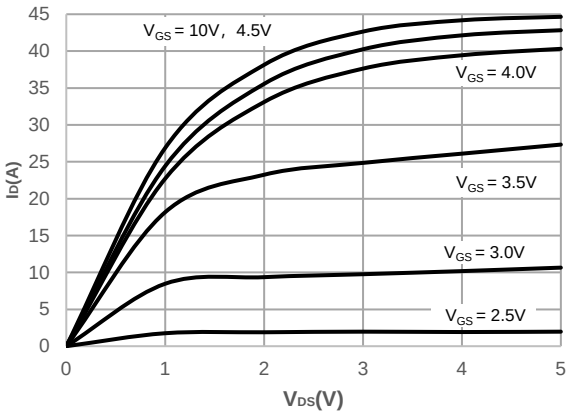


Figure 6: Typical Transfer Characteristics

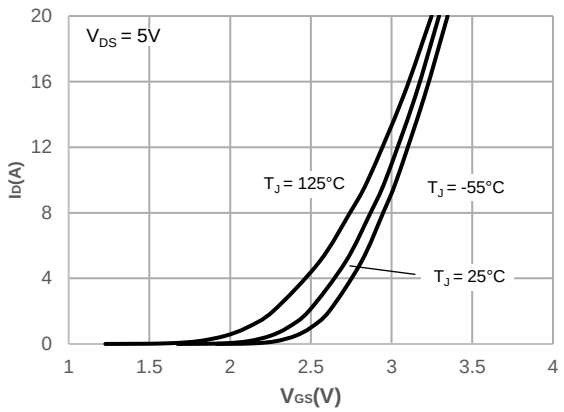


Figure 7: On-resistance vs. Drain Current

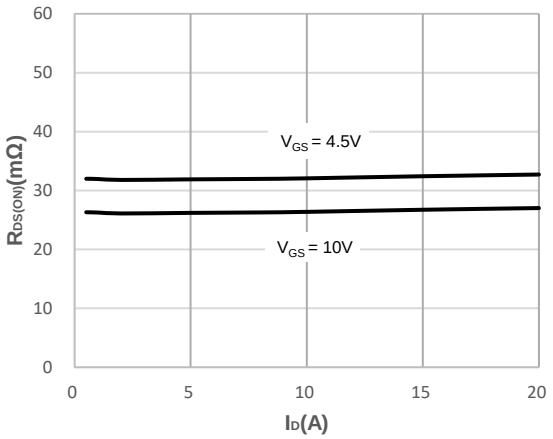


Figure 8: Body Diode Characteristics

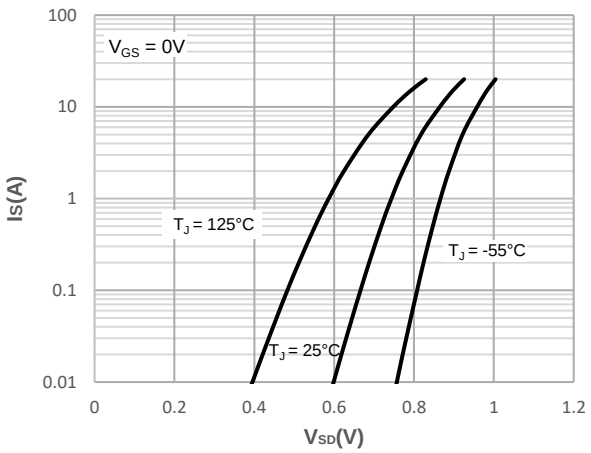


Figure 9: Gate Charge Characteristics

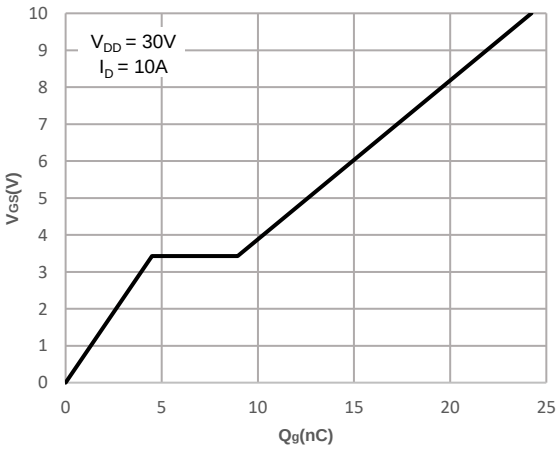
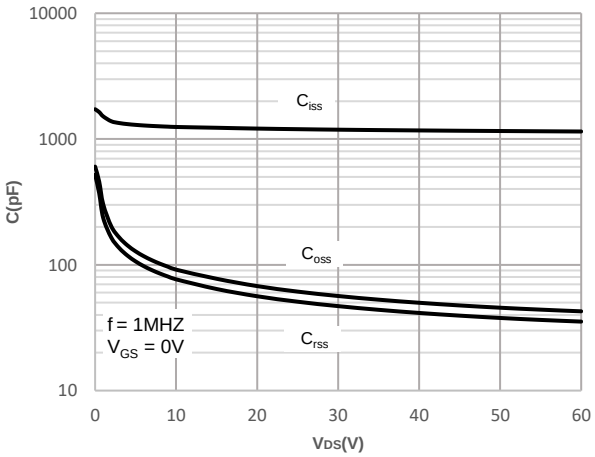


Figure 10: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

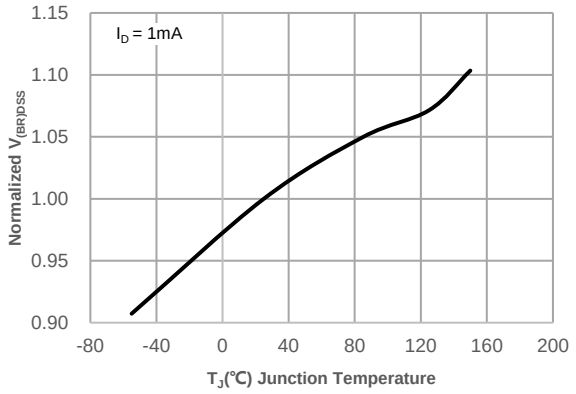


Figure 12: Normalized on Resistance vs. Junction Temperature

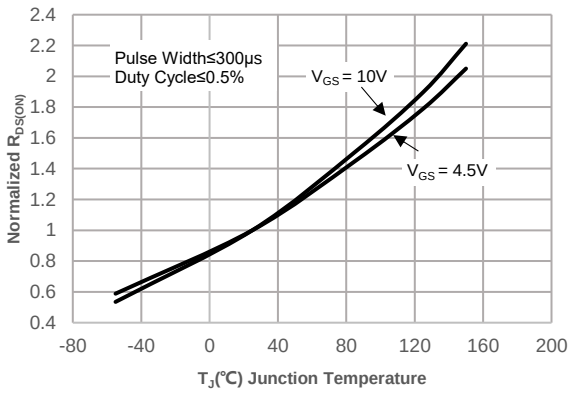


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

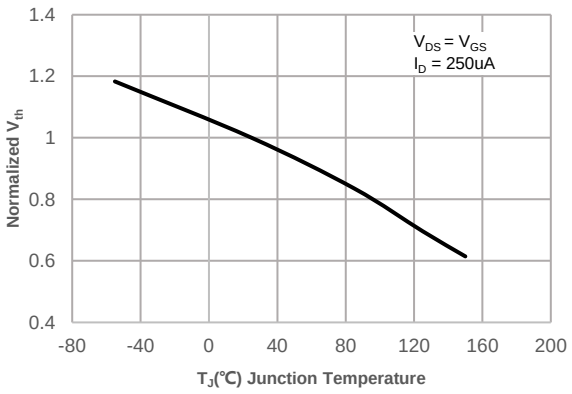
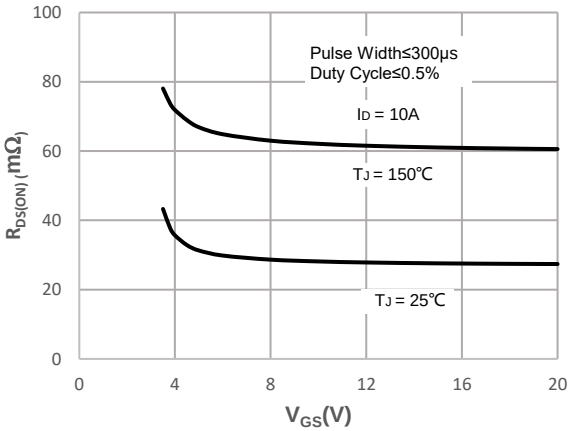


Figure 14: $R_{DS(ON)}$ vs. V_{GS}



Test Circuit

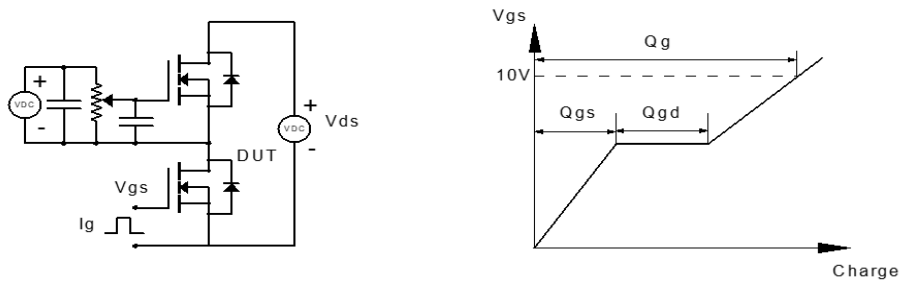


Figure 1: Gate Charge Test Circuit & Waveform

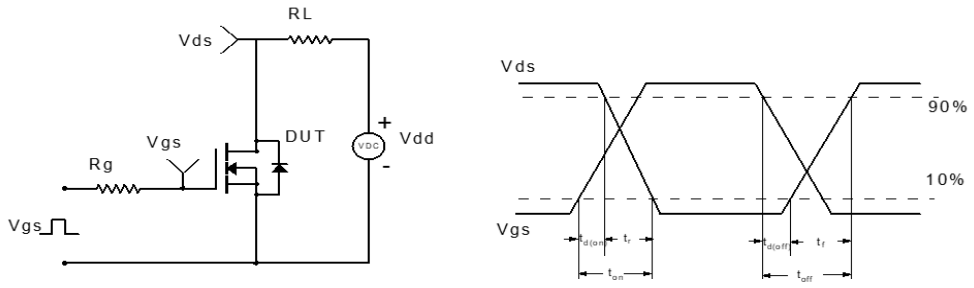


Figure 2: Resistive Switching Test Circuit & Waveform

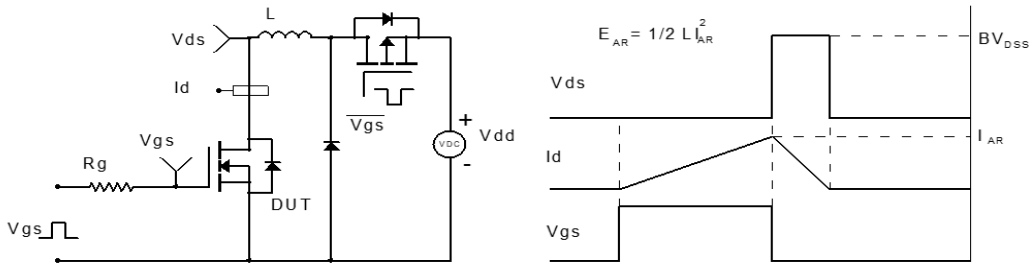


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

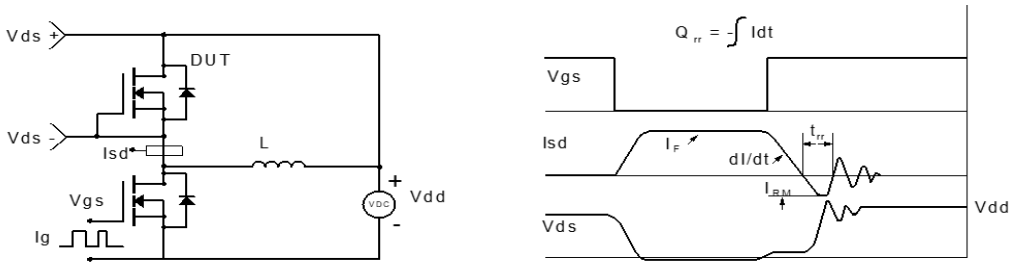
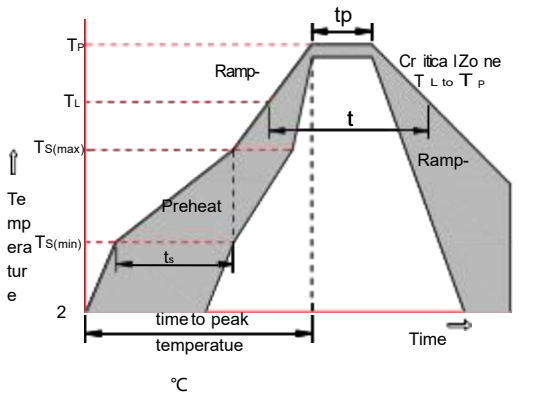


Figure 4: Diode Recovery Test Circuit & Waveform

Soldering parameters

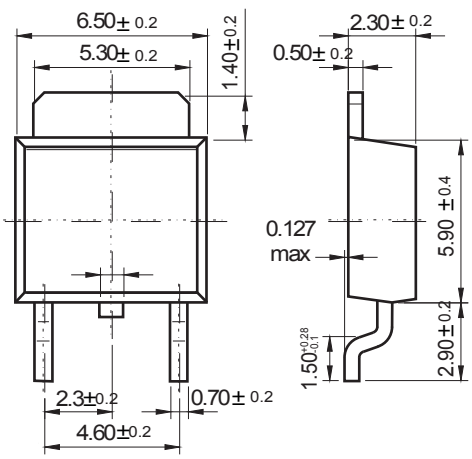
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition

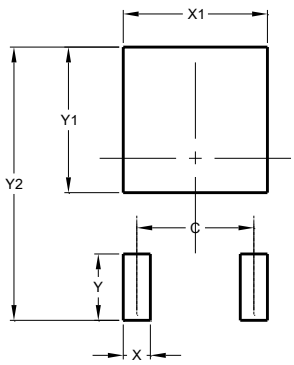


Package Dimensions & Suggested Pad Layout

TO-252



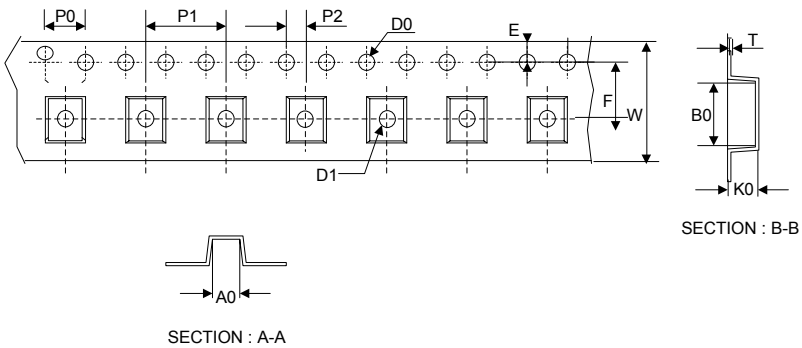
Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

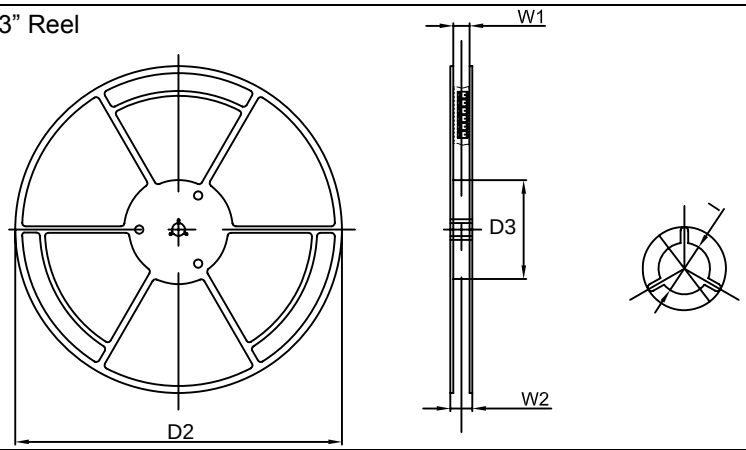
Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.15
D1	1.55±0.20
E	1.75±0.20
F	7.50±0.20
W	16.00±0.20
A0	7.10±0.20
B0	10.50±0.20
K0	2.70±0.20
T	0.30±0.10

13” Reel



Symbol	Dimension (mm)
D2	330.0±5.0
D3	100.0±4.0
W1	20.0±5.0
W2	25.0±5.0
I	13.0±2.0

Quantity: 2500PCS